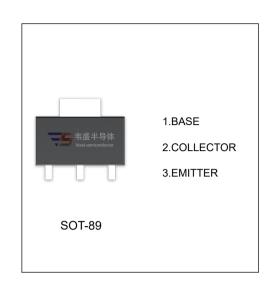


2SD2098 FEATURES

- Excellent DC current gain characteristics
- Complements the 2SB1386

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	50	V	
V _{CEO}	Collector-Emitter Voltage 20			
V _{EBO}	Emitter-Base Voltage	6	V	
Ic	Collector Current -Continuous	5	А	
Pc	Collector Power Dissipation	500	mW	
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~150	℃	



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA,I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =40V,I _E =0			0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V,I _C =0			0.5	μA
DC current gain	h _{FE}	V _{CE} =2V,I _C =0.5A	120		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =4A,I _B =100mA			1	V
Transition frequency	f⊤	V _{CE} =6V,I _C =50mA,f=100MHz		150		MHz
Collector output capacitance	C _{ob}	V _{CB} =20V,I _E =0,f=1MHz		30		pF

CLASSIFICATION OF hFE

Rank	Q	R
Range	120-270	180-390
Marking	AHQ	AHR